

AMENDMENT TO THE CLAIMS:

1 - 11 (Cancelled)

12. (Original) A method for making a body contact in a silicon-on-insulator transistor, said method comprising the steps of:

placing a shallow trench isolation on a substrate between regions of an SOI layer;
depositing a gate conductor over a portion of said substrate;
applying a first dummy gate mask over a first portion of said gate conductor;
etching said gate conductor such that said gate conductor not comprising said first portion of said gate conductor is removed;
depositing an insulator on said substrate;
polishing said insulator;
applying a second gate mask over a second portion of said gate conductor;
etching said gate conductor such that said gate conductor not comprising said second portion of said gate conductor is removed;
depositing spacer portions on said substrate such that said spacer portions isolate said second portion of said gate conductor and said insulator from the rest of said transistor;
depositing charged implants in said substrate.

13. (Original) The method of claim 12 wherein said insulator is an oxide.

14. (Original) The method of claim 12 wherein said insulator is a nitride.

15. (Original) A method of reducing capacitance in a silicon-on-insulator transistor, said transistor having a source region, a drain region, a body-contact region, and a gate connecting said source region to said drain region, said method comprising the step of isolating said body-contact region from said source region and said drain region.

16. (Original) The method of claim 15 wherein said step of isolating said body-contact region is accomplished by replacing a portion of said gate with an insulator.

17. (Original) The method of claim 15 wherein said step of isolating said body-contact region is accomplished by substituting, during fabrication, an insulator for at least a portion of said gate.

18. (Original) The method of claim 15 wherein said step of isolating said body-contact region is accomplished by forming a thick layer of insulative material between said gate and said body-contact region.

19. (Original) The method of claim 15 wherein said step of isolating said body-contact region is accomplished by forming, during fabrication, a gap between said body-contact region and said source region and said drain region.

20. (Original) The method of claim 19 wherein said gap is created by preventing the formation of conductive material in a region between said body-contact region and said source